

IN THE SPECIFICATION

Please amend the Specification as follows:

Please amend the paragraph beginning on page 2, line 20 as follows:

In recent years, a method for forming an InGaP layer by breaking a natural superlattice structure to disorder the arrangement of Ga atoms and In atoms in the Group III atomic layers has been known, for example, as described in ~~Patent Document 2~~ Japanese Laid-Open Patent Application Publication No. 11-243058. Field-effect transistors have been developed in which such InGaP with a broken natural superlattice is used to reduce the interface resistance between an InGaP layer and the adjacent semiconductor layers.

Please amend the paragraph beginning on page 15, line 11 as follows:

The terminal of the resistive element **42** opposite to the gate electrode side is connected to a control terminal **41** **43** to which a direct voltage (direct bias) is applied.

Please amend the paragraph beginning on page 17, line 4 as follows:

In this way, the field-effect transistor **42** **41** having the same structure as that of the first embodiment is used to control the on/off state of the switching circuit **50** in accordance with the control voltage applied to each of the control terminals **43A** and **43B**. Therefore, a burst failure due to the frequency dispersion of the drain current can be prevented. Hence, a pair of field-effect transistors **42** **41** can be certainly switched between the on state and the off state. As a result, very excellent switching characteristics can be achieved.